



# BUK9M35-80E

N-channel 80 V, 35 mΩ logic level MOSFET in LPAK33

19 September 2016

Product data sheet

## 1. General description

Logic level N-channel MOSFET in an LPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)}$  rating of greater than 0.5 V at 175 °C

## 3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

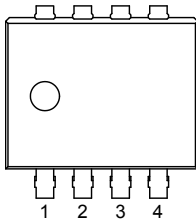
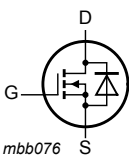
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	80	V
$I_D$	drain current	$V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	-	26	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	62	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	28	35	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 10\text{ A}$ ; $V_{DS} = 64\text{ V}$ ; $V_{GS} = 5\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>	-	4.9	-	nC



## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source	 LPAK33 (SOT1210)	 mbb076
2	S	Source		
3	S	Source		
4	G	Gate		
mb	D	Mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9M35-80E	LPAK33	Plastic single ended surface mounted package (LPAK33); 8 leads	SOT1210

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M35-80E	93580E

## 8. Limiting values

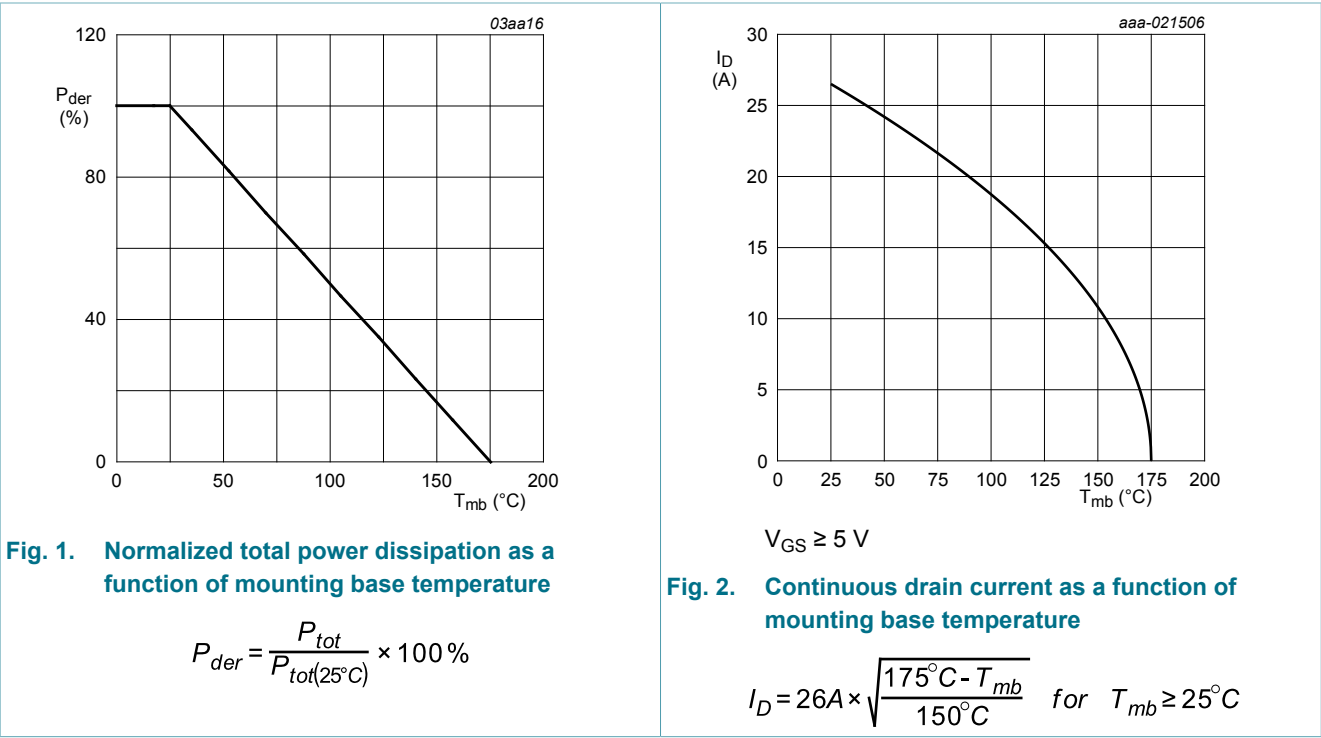
Table 5. Limiting values

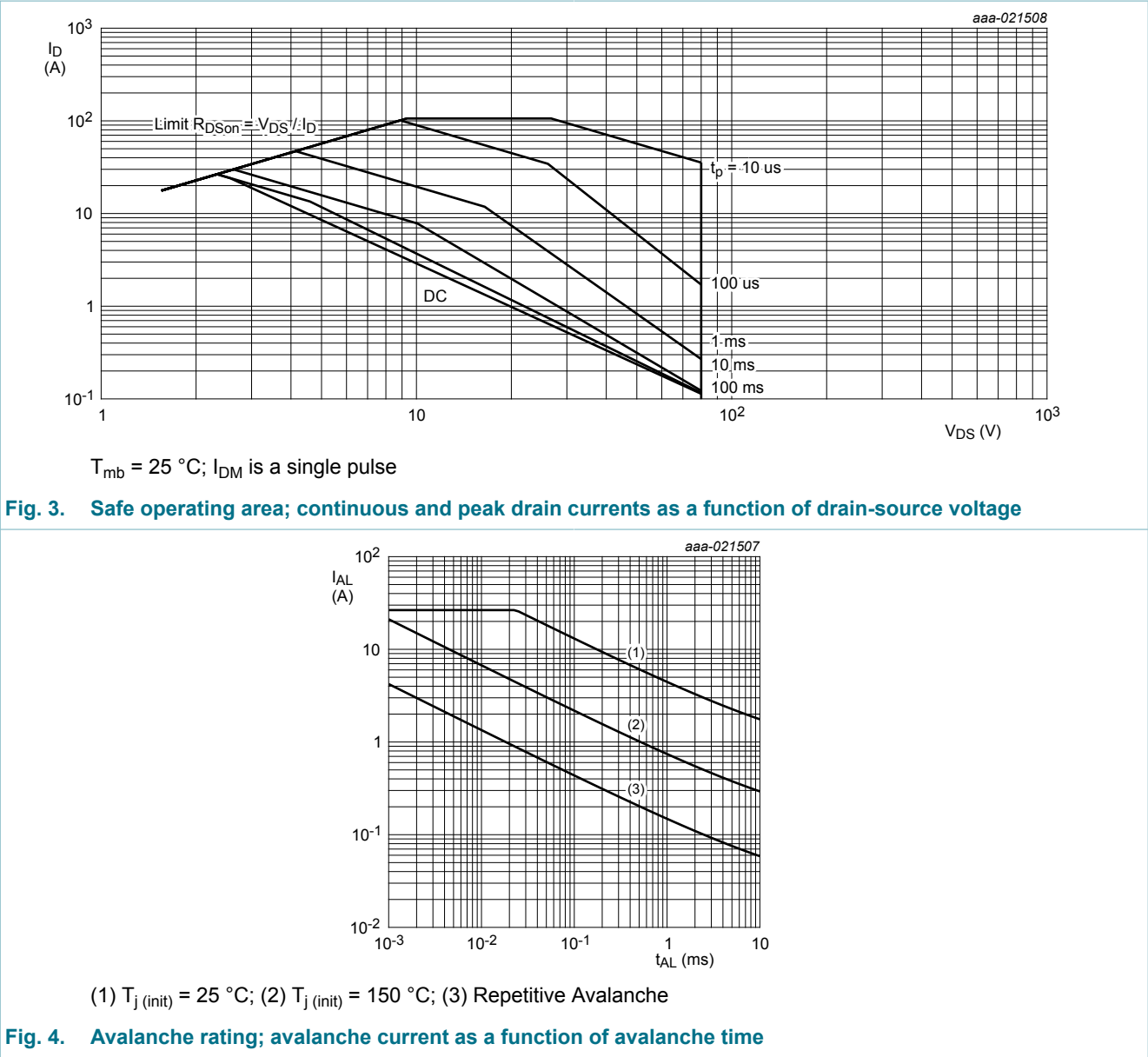
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	80	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	80	V
$V_{GS}$	gate-source voltage	DC; $T_j \leq 175\text{ °C}$	-10	10	V
		Pulsed; $T_j \leq 175\text{ °C}$	-15	15	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; Fig. 1	-	62	W
$I_D$	drain current	$V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 2	-	26	A
		$V_{GS} = 5\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 2	-	19	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 3	-	106	A

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	26	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	106	A
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 26 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped; <a href="#">Fig. 4</a>	<a href="#">[3][4]</a>	-	32.3	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T<sub>j</sub> and or V<sub>GS</sub>
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.





9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	2.01	2.43	K/W

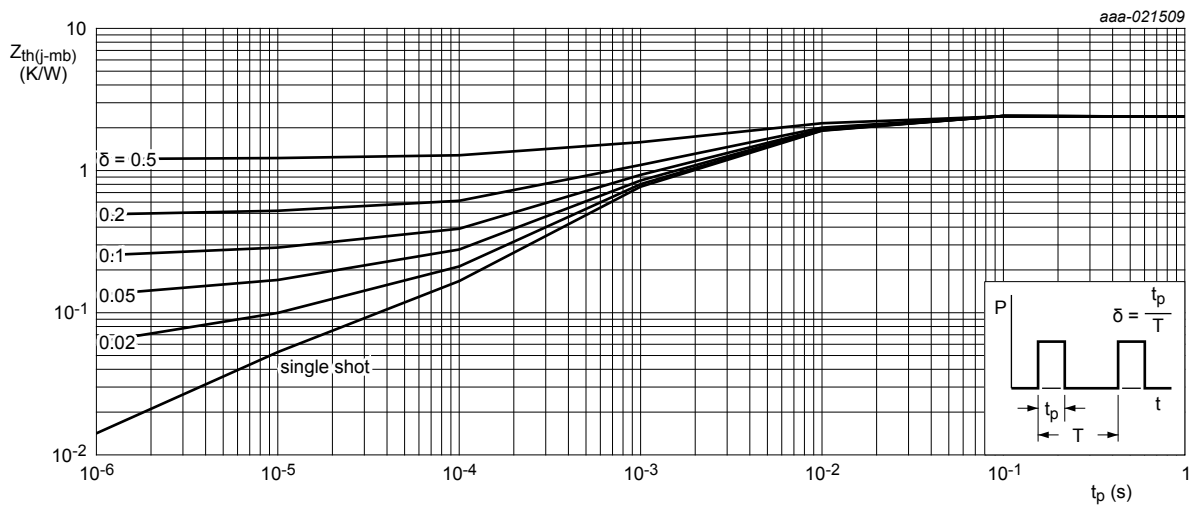


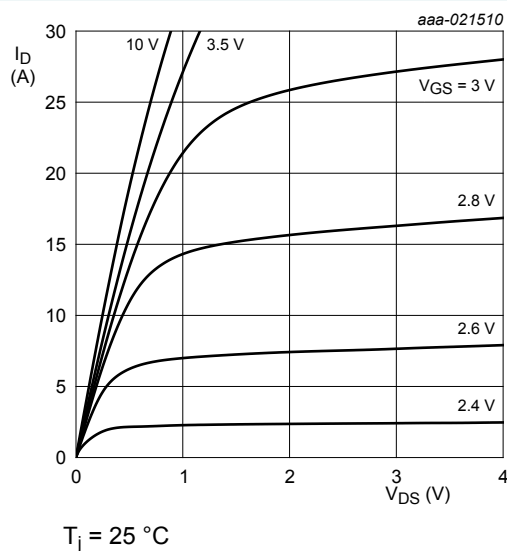
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

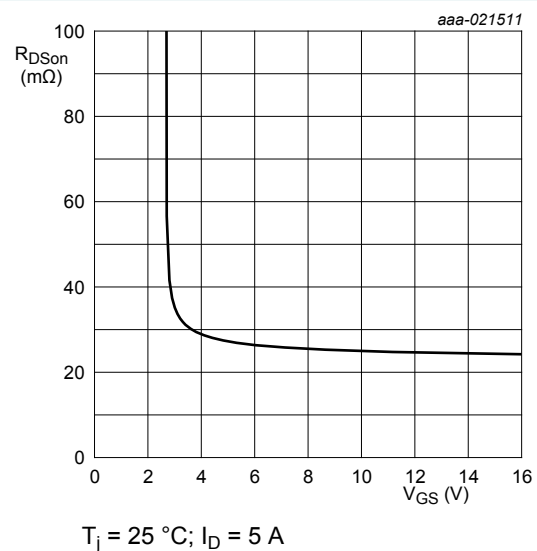
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		80	-	-	V
		$I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -55\text{ }^\circ\text{C}$		72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>		1.4	1.7	2.1	V
		$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	-	2.45	V
		$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>		0.5	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 80\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		-	0.01	1	$\mu\text{A}$
		$V_{DS} = 80\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 175\text{ }^\circ\text{C}$		-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 10\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		-	2	100	nA
		$V_{GS} = -10\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	28	35	m $\Omega$
		$V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	25	31	m $\Omega$
		$V_{GS} = 5\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>		-	-	88	m $\Omega$
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 10\text{ A}$ ; $V_{DS} = 64\text{ V}$ ; $V_{GS} = 5\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	13.5	-	nC
$Q_{GS}$	gate-source charge			-	3.3	-	nC
$Q_{GD}$	gate-drain charge			-	4.9	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>		-	1356	1804	pF
C <sub>oss</sub>	output capacitance			-	106	127	pF
C <sub>rss</sub>	reverse transfer capacitance			-	52	71	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 60 V; R <sub>L</sub> = 5 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C		-	8.8	-	ns
t <sub>r</sub>	rise time			-	14	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	19.5	-	ns
t <sub>f</sub>	fall time			-	12	-	ns
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>		-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 10 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C		-	21	-	ns
Q <sub>r</sub>	recovered charge			-	21.6	-	nC



**Fig. 6.** Output characteristics; drain current as a function of drain-source voltage; typical values



**Fig. 7.** Drain-source on-state resistance as a function of gate-source voltage; typical values

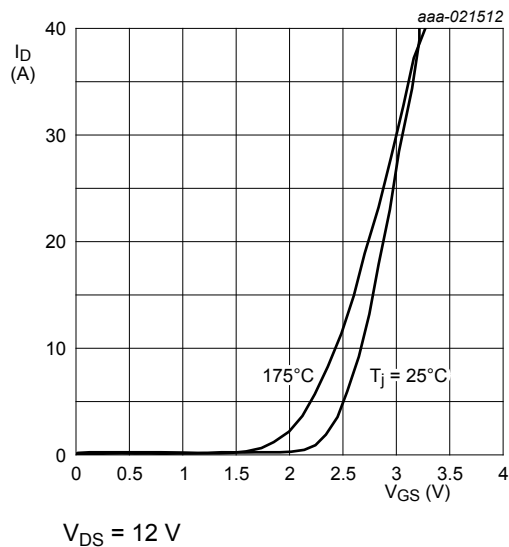


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

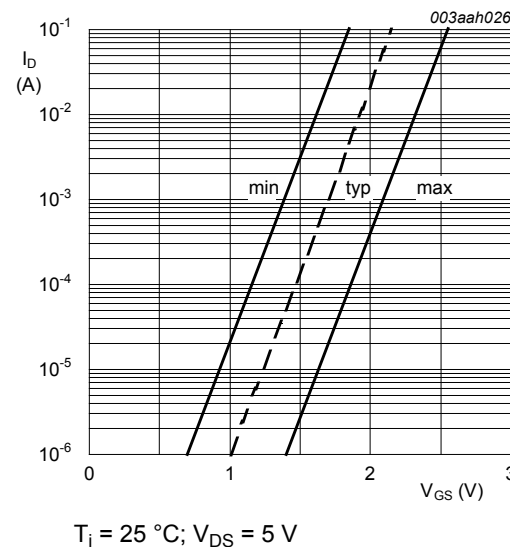


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

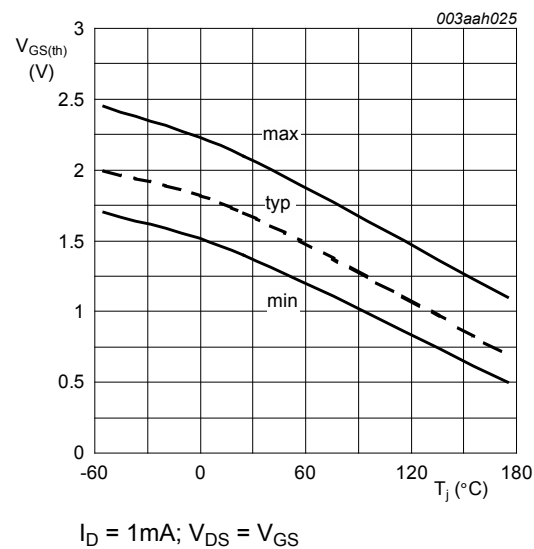


Fig. 10. Gate-source threshold voltage as a function of junction temperature

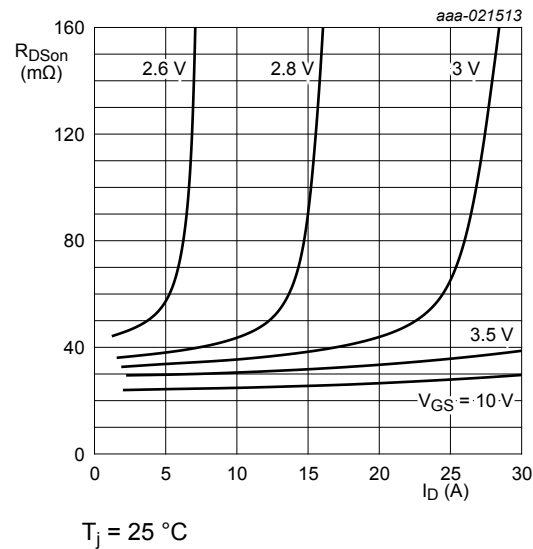


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

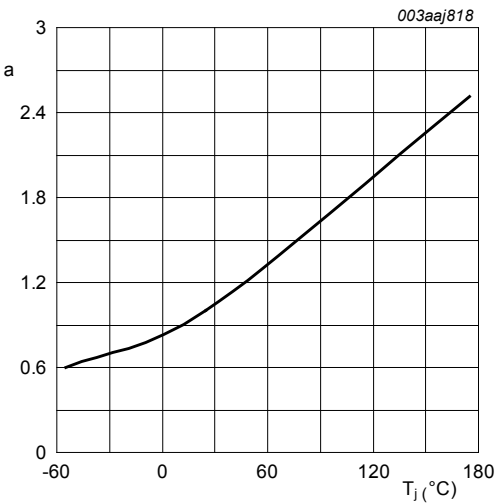
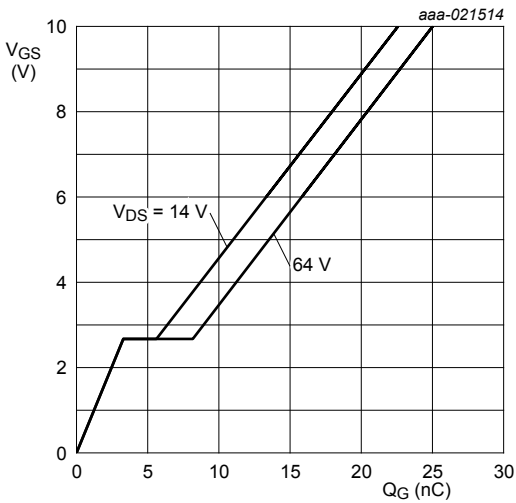


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



$T_j = 25^{\circ}C$ ;  $I_D = 10\text{ A}$

Fig. 13. Gate-source voltage as a function of gate charge; typical values

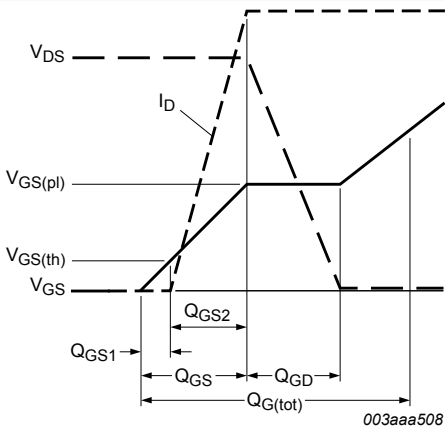
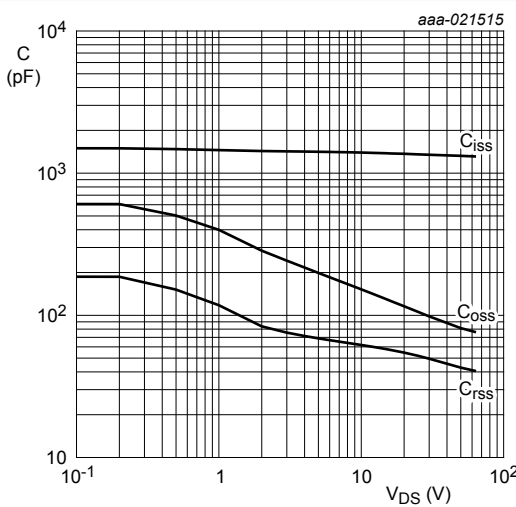


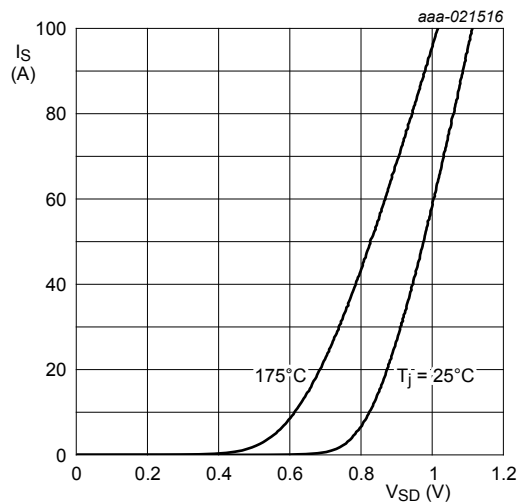
Fig. 14. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$ ;  $f = 1\text{ MHz}$

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





$V_{GS} = 0\text{ V}$

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## 11. Application information

For guidance on how to use and understand this datasheet, please refer to application note [AN11158](#) "Understanding power MOSFET datasheet parameters".

12. Package outline

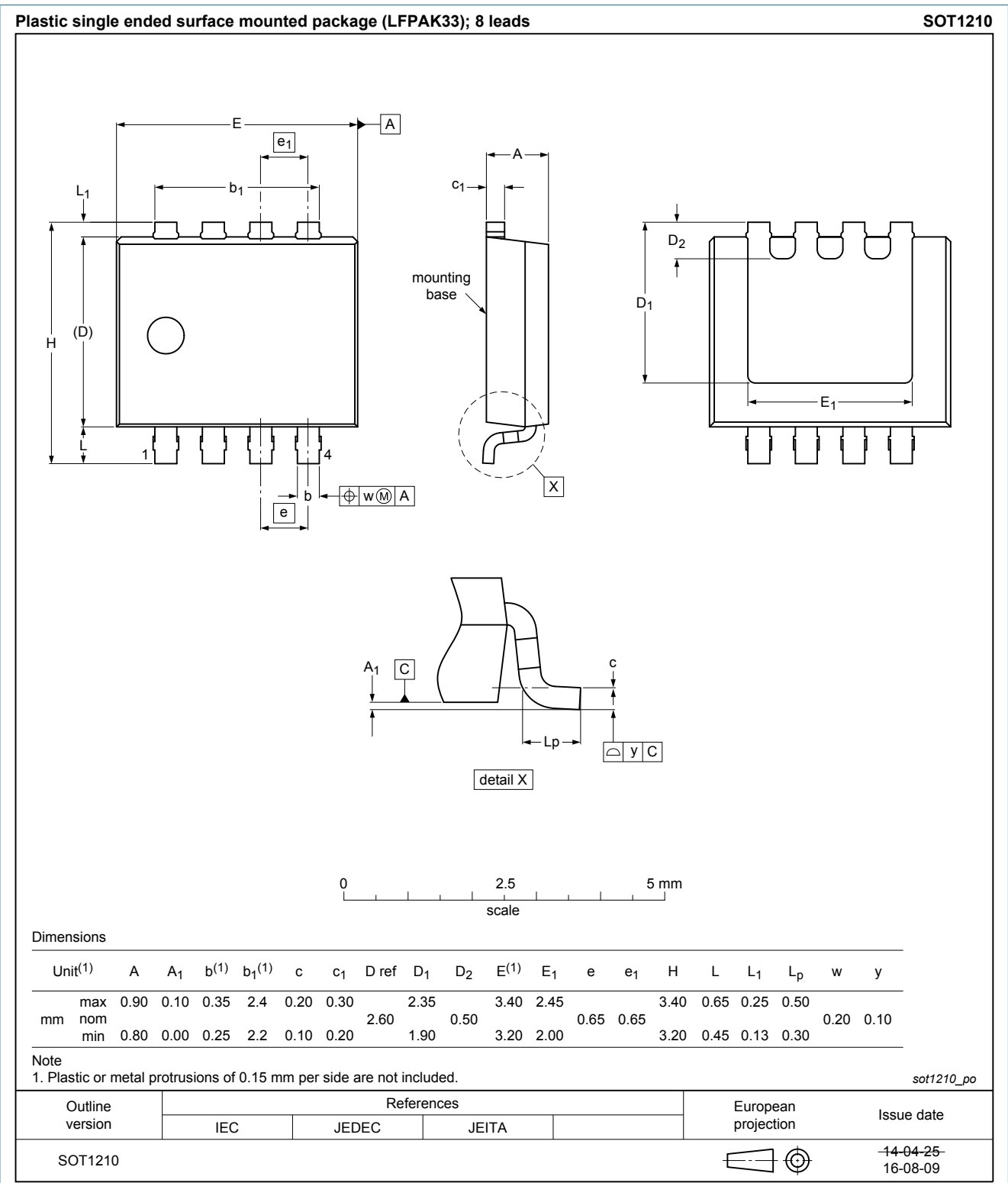


Fig. 17. Package outline LPAK33 (SOT1210)

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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